

N-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY							
V _{DS} (V)	R _{DS(on)} (mΩ) (TYP.)	I _D (A)	Q _g (TYP.)				
100	1.7 at V _{GS} = 10 V	280	134 nC				

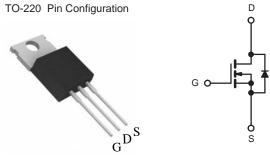
FEATURES

- DT-TrenchPower MOSFET
- 100 % R_q and UIS tested



APPLICATIONS

- Power supplies:
 - Uninterruptible power supplies
 - AC/DC switch-mode power supplies
 - Lighting
- Synchronous rectification
- DC/DC converter
- Motor drive switch
- DC/AC inverter
- Battery management



N-Channel	MOSFF"

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)							
PARAMETER PARAMETER	SYMBOL	LIMIT	UNIT				
Drain-Source Voltage	V _{DS}	100	,,				
Gate-Source Voltage	V _{GS}	± 20	V				
0 11	T _C = 25 °C		280				
Continuous Drain Current (T _J = 150 °C)	T _C = 100 °C	l _D	153				
Pulsed Drain Current (t = 100 μs)	I _{DM}	1120	A				
Avalanche Current	l 0.1 mll	I _{AS}	155				
Single Avalanche Energy ^a	L = 0.1 mH	E _{AS}	2388	mJ			
Manipular Davier Dissipation 3	T _C = 25 °C	В	415 b	w			
Maximum Power Dissipation ^a	T _C = 100 °C	P _D	166 ^b	vv			
Operating Junction and Storage Temperature F	T _J , T _{sta}	-55 to +150	°C				

THERMAL RESISTANCE RATINGS							
PARAMETER	SYMBOL	LIMIT	UNIT				
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	65	°C/W				
Junction-to-Case (Drain)	R _{thJC}	0.35	C/VV				

Notes

- a. Duty cycle $\leq 1 \%$.
- b. See SOA curve for voltage derating.
- c. When mounted on 1" square PCB (FR4 material).



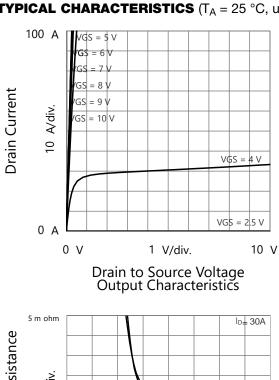
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)								
PARAMETER SYMBO		TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT		
Static								
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS}=0~V,~I_D=250~\mu A$	100	-	-	V		
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS},I_D=250\;\mu A$	2	-	4	V		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA		
		$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1			
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} = 100 V, V_{GS} = 0 V, T_J = 55 °C	-	-	10	μΑ		
		$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 125 ^{\circ}\text{C}$	-	-	2	mA		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \geq 10~V,~V_{GS} = 10~V$	280	-	-	Α		
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}$	-	1.7	2.2	mΩ		
Forward Transconductance a	9 _{fs}	$V_{DS} = 10 \text{ V}, I_D = 30 \text{ A}$	-	65	-	S		
Dynamic ^b								
Input Capacitance	C _{iss}		-	10800	-	pF		
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 50 \text{ V}, f = 1 \text{ MHz}$	-	1860	-			
Reverse Transfer Capacitance	C _{rss}		-	52	-			
Total Gate Charge ^c	Q_g		-	166	-	nC		
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}$	-	36	-			
Gate-Drain Charge ^c	Q_{gd}		-	35	-			
Gate Resistance	R_g	f = 1 MHz	-	1.4	-	Ω		
Turn-On Delay Time ^c	t _{d(on)}		-	43	-			
Rise Time ^c	t _r	V_{DD} = 50 V, R_L = 1.67 Ω	-	52	-			
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 30 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	107	-	ns		
Fall Time ^c	t _f		-	79	-			
Drain-Source Body Diode Ratings ar	nd Characteri	stics ^b (T _C = 25 °C)						
Pulsed Current (t = 100 μs)	I _{SM}		-	-	1120	Α		
Forward Voltage ^a	V_{SD}	I _F = 30 A, V _{GS} = 0 V	-	-	1.2	V		
Reverse Recovery Time	t _{rr}		-	88	-	ns		
Peak Reverse Recovery Charge	I _{RM(REC)}	$I_F = 30 \text{ A, di/dt} = 100 \text{ A/}\mu\text{s}$	-	5	-	Α		
Reverse Recovery Charge	Q _{rr}		-	300	-	nC		

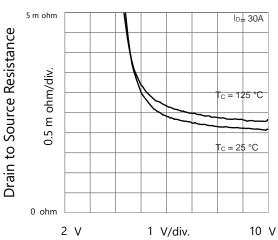
- a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %. b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

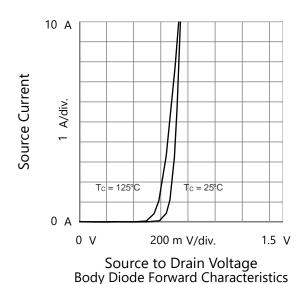


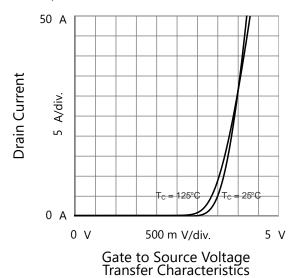
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

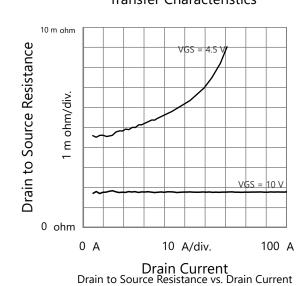


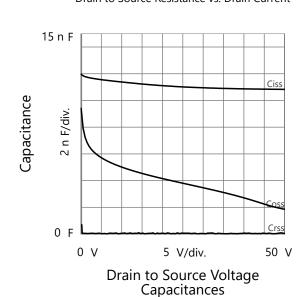


Gate to Source Voltage
Drain to Source Resistance vs. Gate to Source Voltage



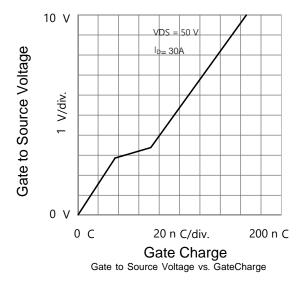


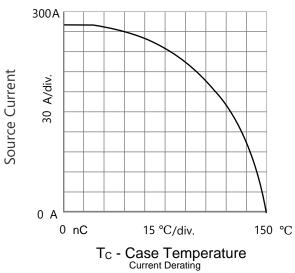


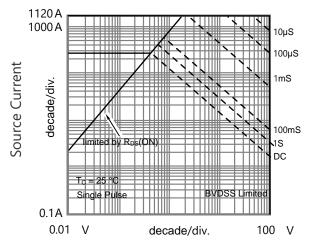




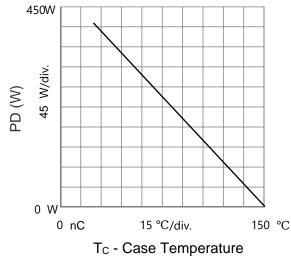
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)







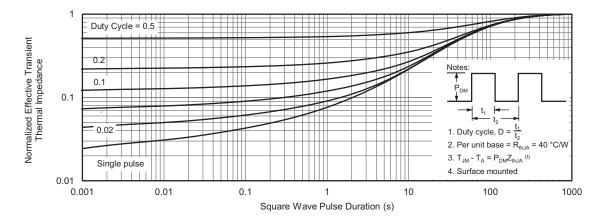
Source to Drain Voltage Safe Operating Area, Junction-to-Ambient



Power Derating



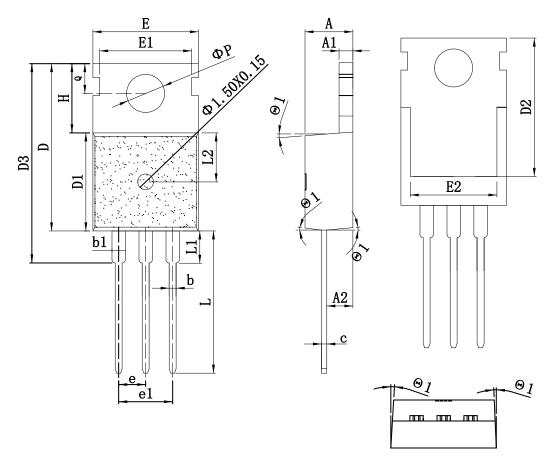
THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



TO-220_3L-A PACKAGE OUTLINE

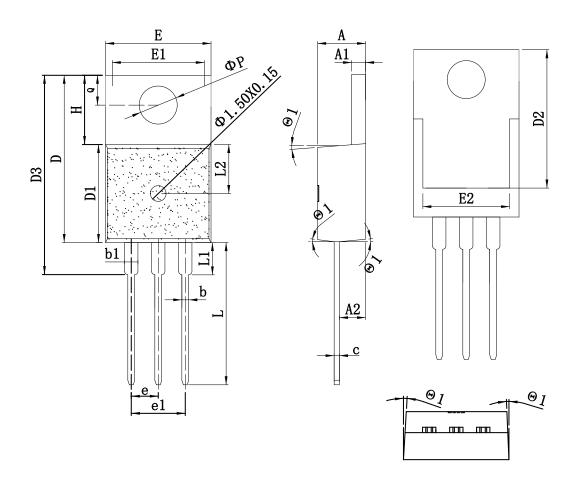


COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

SYMBOL		mm		CAMBOI	SYMBOL mm		
SIMBOL	MIN	TYP	MAX	SIMBOL	MIN	TYP	MAX
A	4.15	4.50	4.80	E1	8.25	8.70	9.15
A1	1.15	1.30	1.50	E2	7.20	8.00	8.80
A2	2.10	2.40	2.65	e	2.38	2.54	2.74
b	0.65	0.80	1.00	e1	5.08REF		
b1	1.10	1.33	1.80	Н	6.20	6.50	6.90
c	0.35	0.50	0.65	L	12.75	13.28	13.70
D	14.25	15.75	16.15	L1	1	-	3.50
D1	8.70	9.20	9.60	L2	2.30	4.65	7.00
D2	12.30	13.10	13.85	φP	3.40	3.65	3.85
D3	16.20	18.80	20.60	Q	2.50	2.80	3.00
Е	8.68	10.02	11.00	θ	2°	-	7°



TO-220_3L-B PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

SYMBOL		mm		CAMBOI	SYMBOL mm		
SIMBOL	MIN	TYP	MAX	SIMBOL	MIN	TYP	MAX
A	4.15	4.50	4.80	E1	8.25	8.70	9.15
A1	1.15	1.30	1.50	E2	7.20	8.00	8.80
A2	2.10	2.40	2.65	e	2.38	2.54	2.74
b	0.65	0.80	1.00	e1	5.08REF		
b1	1.10	1.33	1.80	Н	6.20	6.50	6.90
c	0.35	0.50	0.65	L	12.75	13.28	13.70
D	14.25	15.75	16.15	L1	-	-	3.50
D1	8.70	9.20	9.60	L2	2.30	4.65	7.00
D2	12.30	13.10	13.85	φP	3.40	3.65	3.85
D3	16.20	18.80	20.60	Q	2.50	2.80	3.00
Е	8.68	10.02	11.00	θ	2°	-	7°





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